

A close-up, microscopic view of a VLSI chip. The chip surface is covered in a dense grid of small, square, yellowish-gold pads. A blue, rectangular probe or test head is positioned over the chip, with its tip touching one of the pads. The background is a blurred, reddish-brown surface.

Fault Detection in VLSI Manufacturing

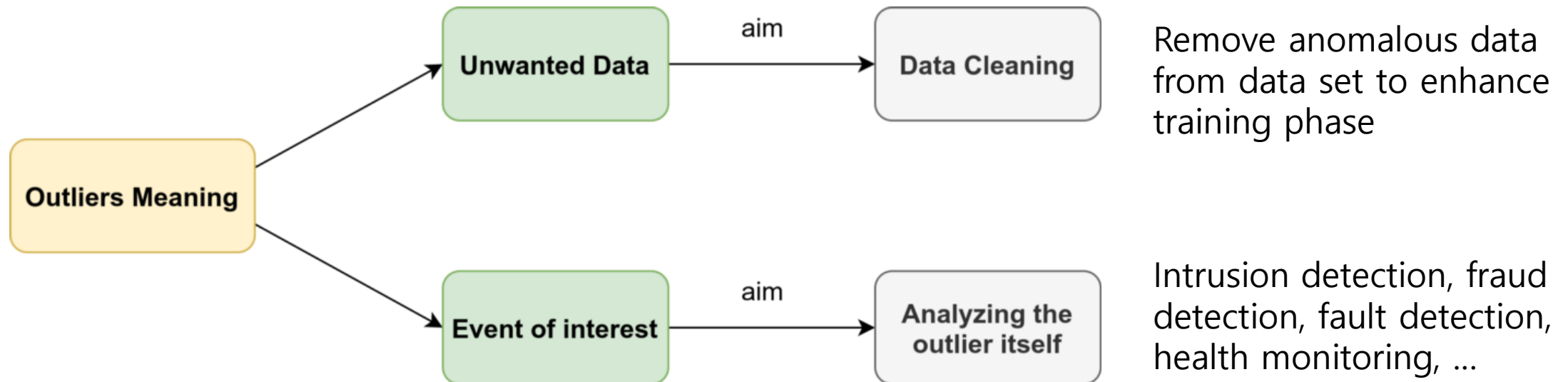
Tran Dai DUONG
AI202216001

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- Paper: Hsu, CY., Liu, WC. **Multiple time-series convolutional neural network for fault detection and diagnosis and empirical study in semiconductor manufacturing.** *J Intell Manuf* **32**, 823–836 (2021). <https://doi.org/10.1007/s10845-020-01591-0>

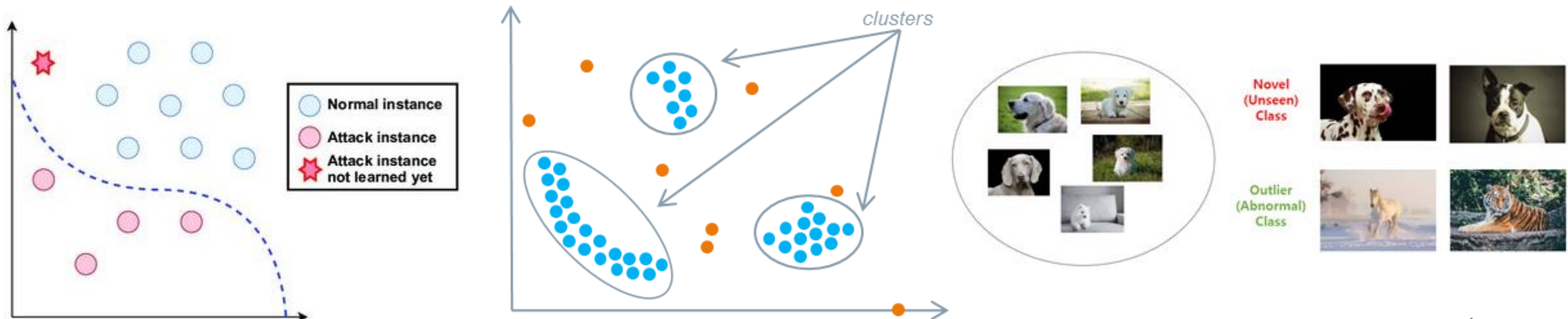
Anomaly Detection basics (1/2)

- Anomaly detection mean identifies data points, events, and/or observations that deviate from a dataset's normal behavior
- There are 2 aspects of Anomaly detection:



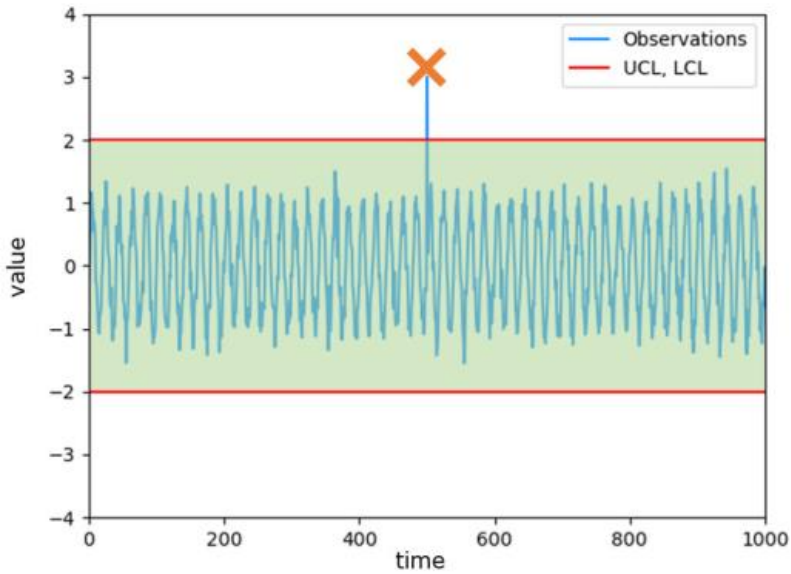
Anomaly Detection basics (2/2)

- There are 3 categories of Anomaly detection:
 - Supervised anomaly detection techniques require a data set that has been labeled as "normal" and "abnormal" and involves training a classifier
 - Unsupervised anomaly detection techniques assume the data is unlabelled
 - Semi-supervised anomaly detection techniques assume that some portion of the data is labelled

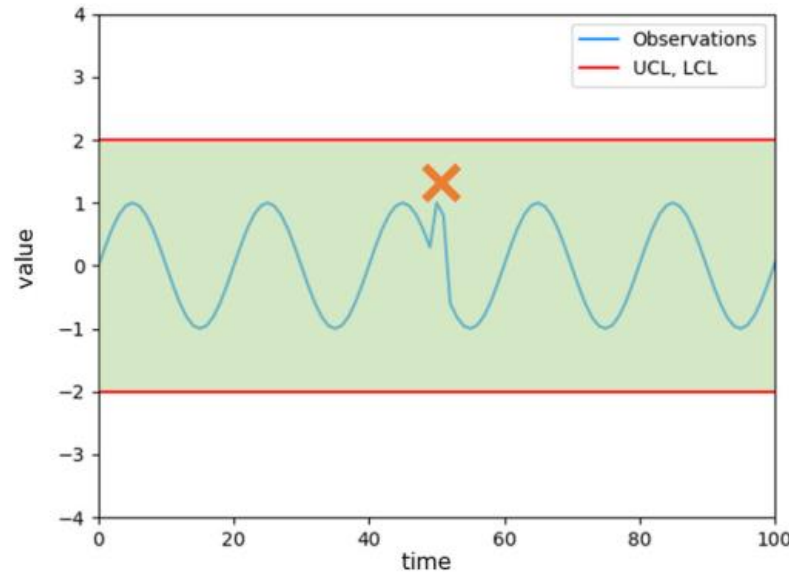


Anomaly Detection in time-series (1/3)

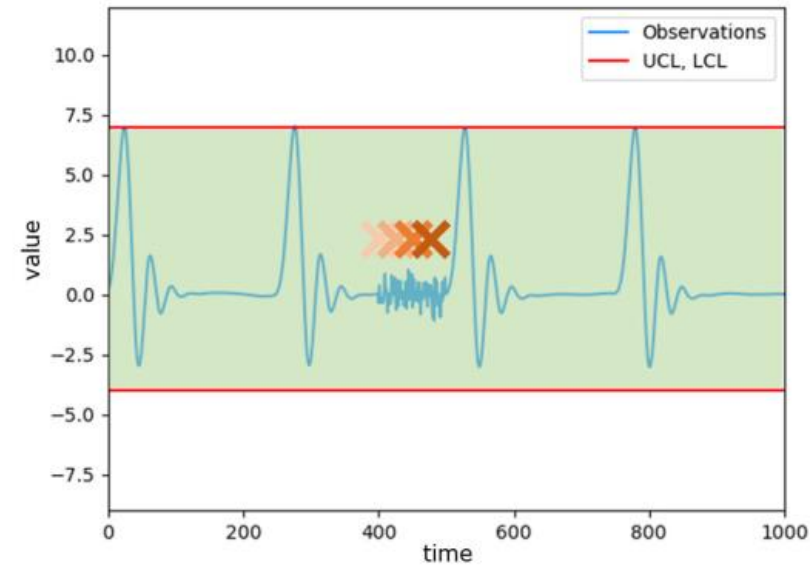
- Anomaly types in time-series data



(a) point anomaly



(b) contextual anomaly



(c) collective anomaly

Anomaly Detection in time-series (2/3)

- Classical approaches:
 - Time/frequency domain analysis by Discrete Fourier Transform (DFT) and Fast Fourier Transform (FFT)
 - Statistical model
 - Distance-based model by Euclidean distance, Dynamic time warping (DTW), Hamming distance
 - Predictive model by autoregressive integrated moving average (ARIMA)
 - Clustering model by k-means, one-class support vector machine (OCSVM), Gaussian mixture model (GMM)
 - Density-based spatial clustering of applications with noise (DBSCAN)

Anomaly Detection in time-series (3/3)

- Modern approaches:

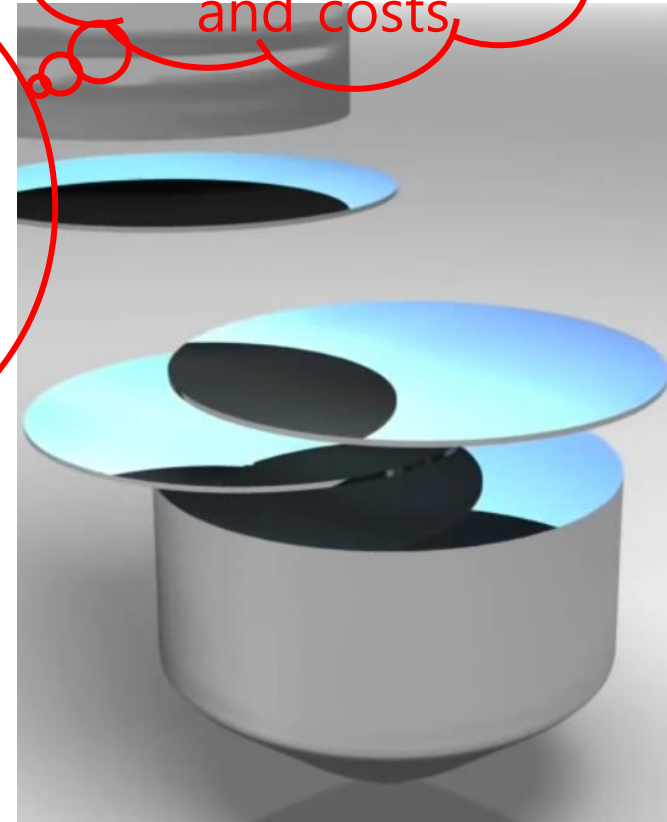
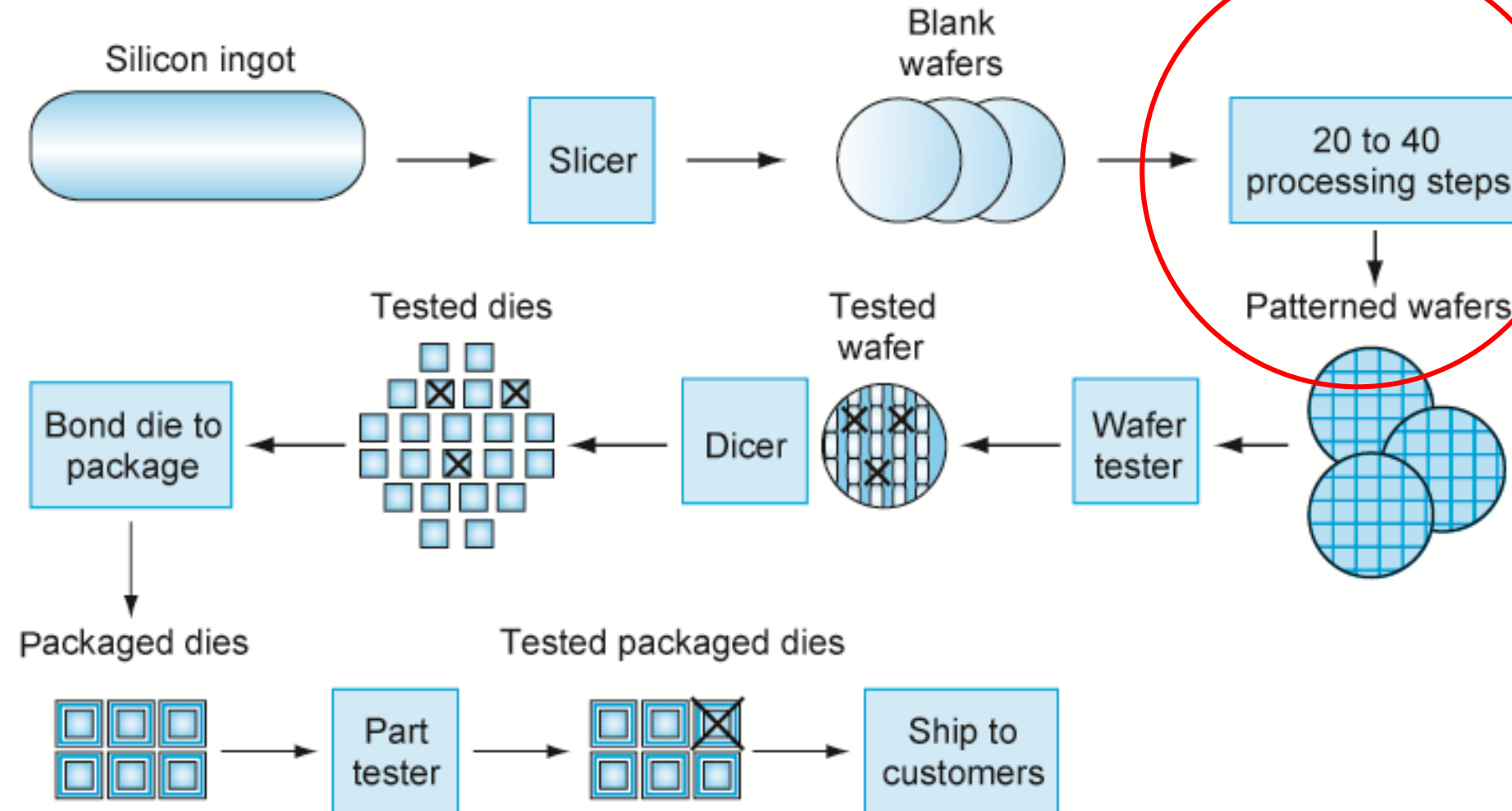
Autoencoder	VAE	RNN
SPREAD (Gugulothu et al., 2018) [104] ●	LSTM-VAE (Park et al., 2018) [112] ●	LSTM-NDT (Hundman et al., 2018) [110] ●
S-RNNs (Kieu et al., 2019) [114] ●	GGM-VAE (Guo et al., 2018) [113] ●	LGMAD (Ding et al., 2019) [111] ●
LSTM-AE (Hsieh et al., 2019) [29] ●	OmniAnomaly (Su et al., 2019) [68] ●	THOC (Shen et al., 2020) [60] ●
MU-Net (Wen et al., 2019) [62] ●		
MSCRED (Zhang et al., 2019) [51] ●		
USAD (Audibert et al., 2020) [72] ●		
GAN	Transformer	TCN
BeatGAN (Zhou et al., 2019) [115] ●	SAnD (Song et al., 2018) [119] ● ●	HS-TCN (Cheng et al., 2019) [116] ●
MAD-GAN (Li et al., 2019) [59] ●	MTSM (Meng et al., 2019) [120] ●	TCN-GMM (Liu et al., 2019) [117] ●
WGAN-based (Choi et al., 2020) [53] ●	GTA* (Chen et al., 2021) [109] ●	TCN-ms (He et al., 2019) [118] ●
RSM-GAN (Khoshnevisan et al., 2020) [74] ●		
	GNN	HTM
	MTAD-GAT (Zhao et al., 2020) [73] ● ●	HTM-based (Wu et al., 2018) [121] ●
	GTA* (Chen et al., 2021) [109] ●	RADM (Ding et al., 2018) [69] ●
	GDN (Deng et al., 2021) [108] ●	

VLSI Manufacturing basics (1/3)

- <https://www.youtube.com/watch?v=aCOyq4YzBtY>

VLSI Manufacturing basics (2/3)

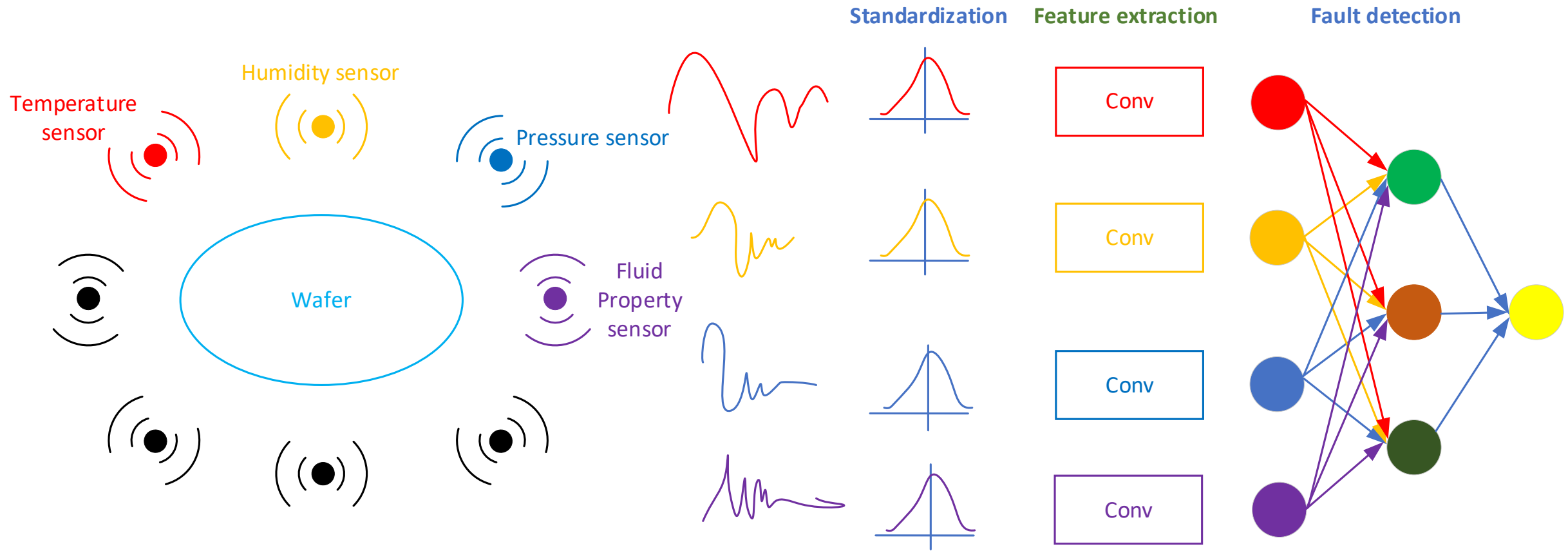
Detecting errors early will save time and costs



VLSI Manufacturing basics (3/3)

	16/12nm	10nm	7nm	5nm
Mass production year and quarter	2015 Q3	2017 Q2	2018 Q3	2020 Q
Capital investment per wafer processed per year	\$11,220	\$13,169	\$14,267	\$16,746
Capital consumed per wafer processed in 2020	\$993	\$1,494	\$2,330	\$4,235
Other costs and markup per wafer	\$2,990	\$4,498	\$7,016	\$12,753
Foundry sale price per wafer	\$3,984	\$5,992	\$9,346	\$16,988
Foundry sale price per chip	\$331	\$274	\$233	\$238

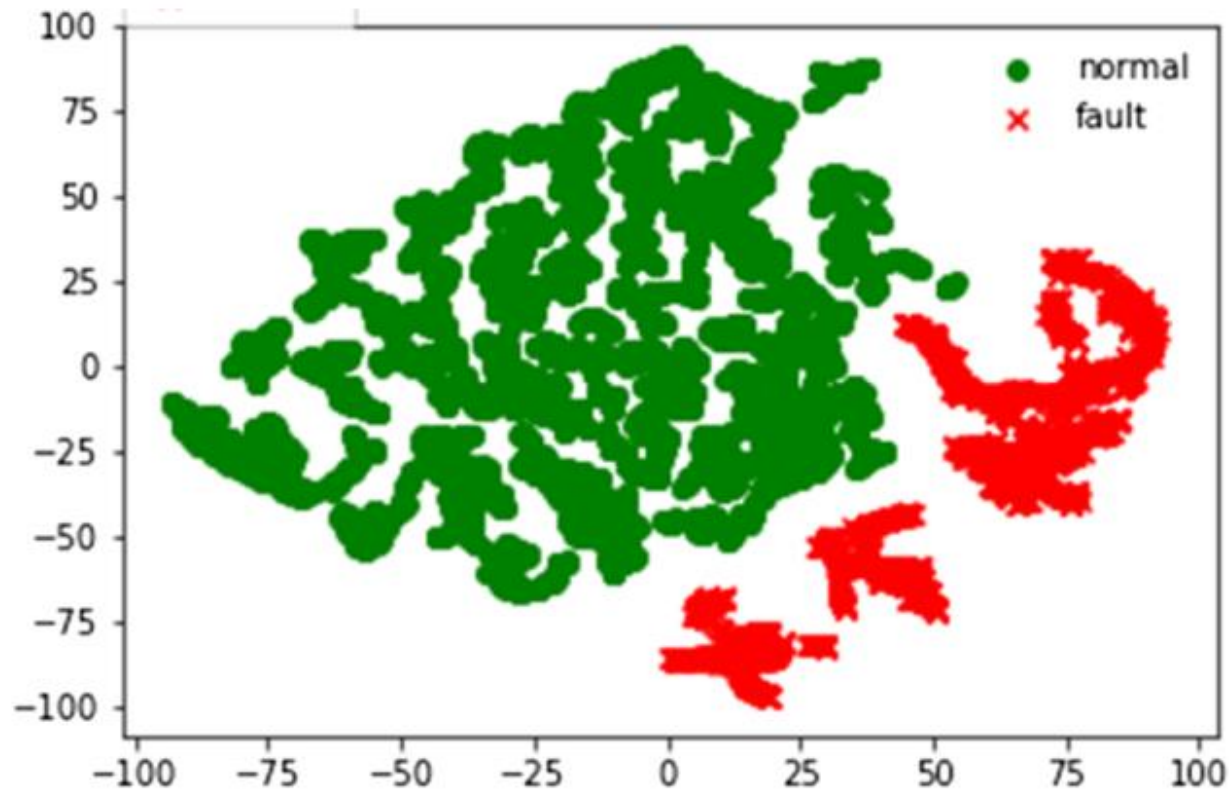
“Multiple time-series convolutional neural network for fault detection and diagnosis and empirical study in semiconductor manufacturing” (1/6)



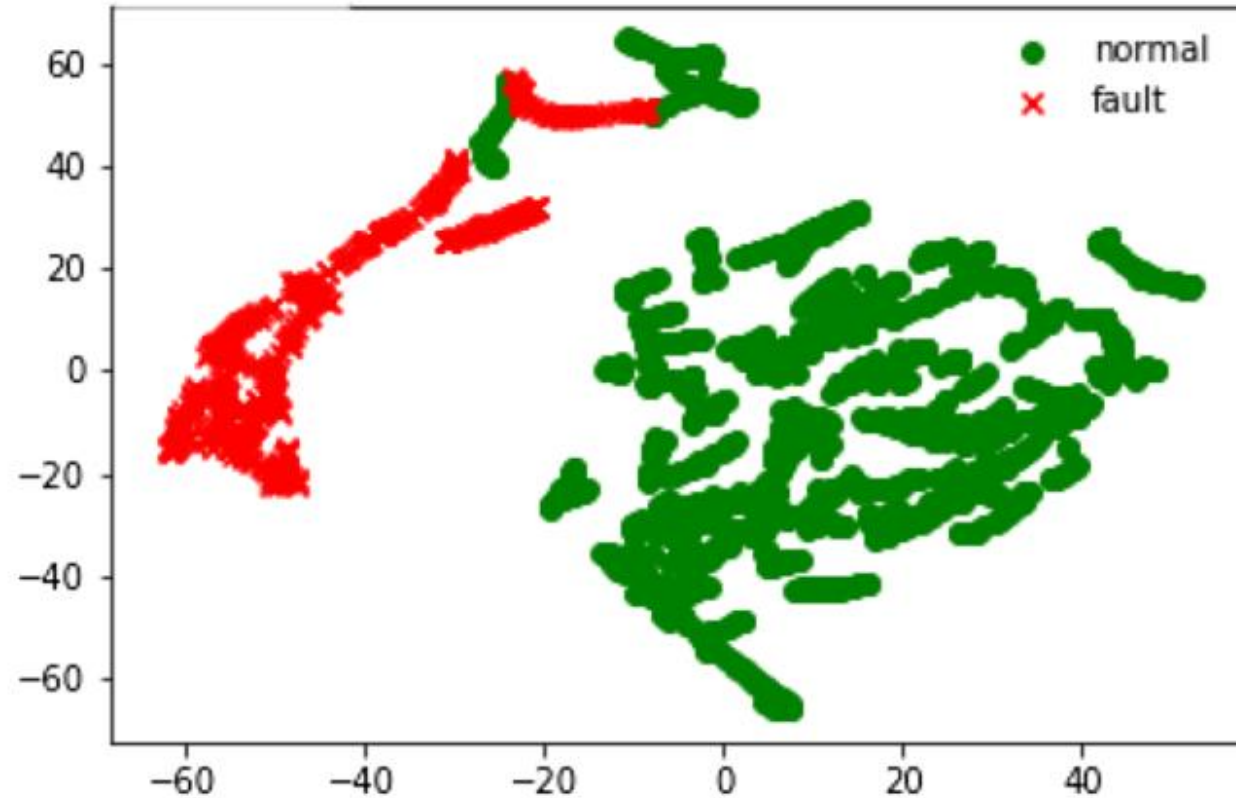
“Multiple time-series convolutional neural network for fault detection and diagnosis and empirical study in semiconductor manufacturing” (2/6)

- Scenario: Fault detection in the Chemical vapor deposition (CVD) process
- Number of sensors: 17
- Type: Supervised anomaly detection
- Time-series anomaly type: Collective anomaly
- Network architecture: CNN-based (MTS-CNN)
 - Kernel size: 5
 - Feature maps: 16 in 1st conv, 64 in 2nd conv
 - Number of CNN (channels): 17
 - Active function: ReLU
 - Pooling method: Average-pooling
 - Learning rate: 0.01; Batch size: 128
 - 0.5 dropout rate to reduce the effect of overfitting
- Dataset: 189 wafers (148 normal wafers, 41 abnormal wafers)
- Time-series: set-3 (Wafer, Data of 17 sensors, record time)

“Multiple time-series convolutional neural network for fault detection and diagnosis and empirical study in semiconductor manufacturing” (3/6)

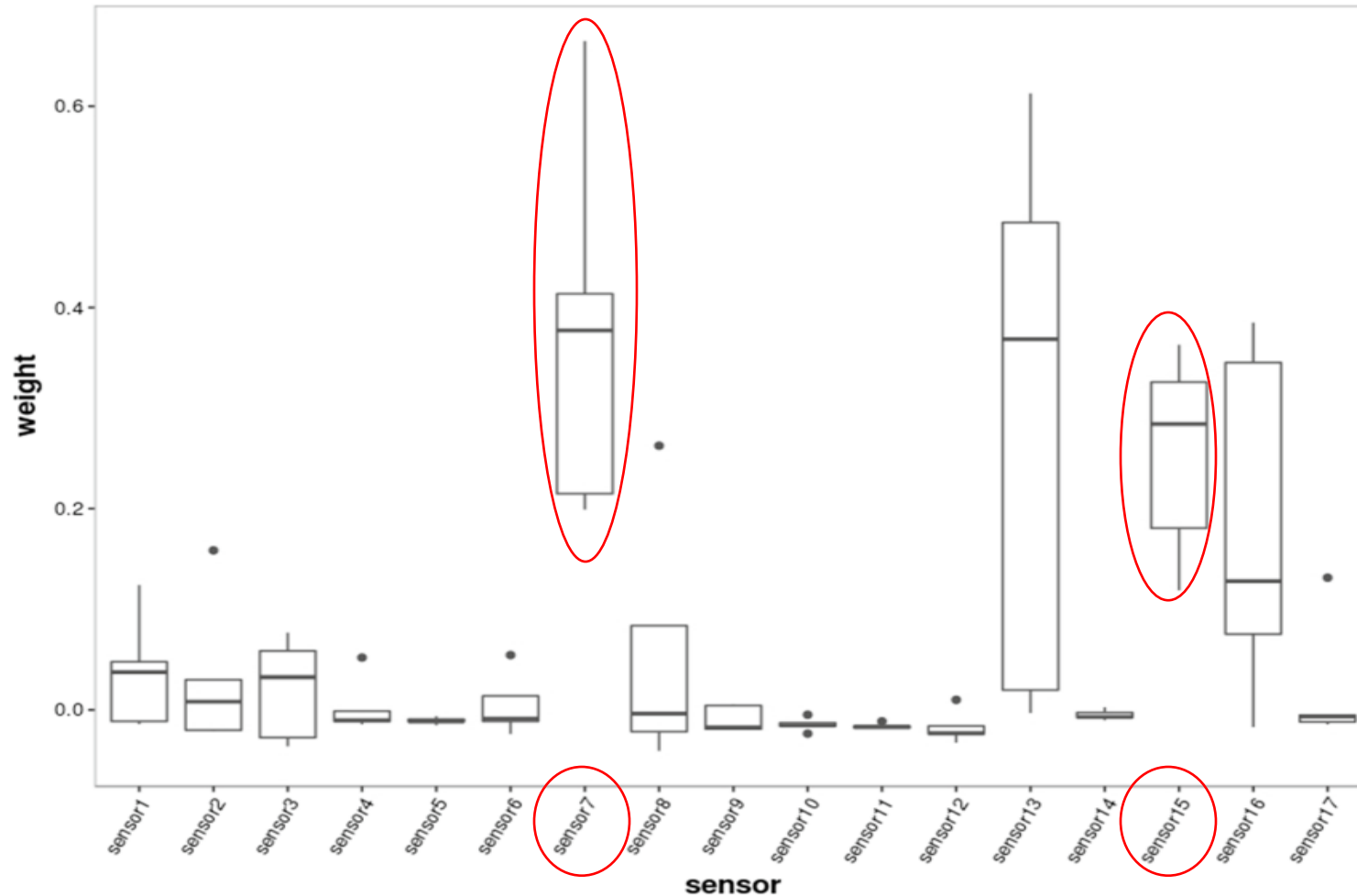


(a) in the training dataset

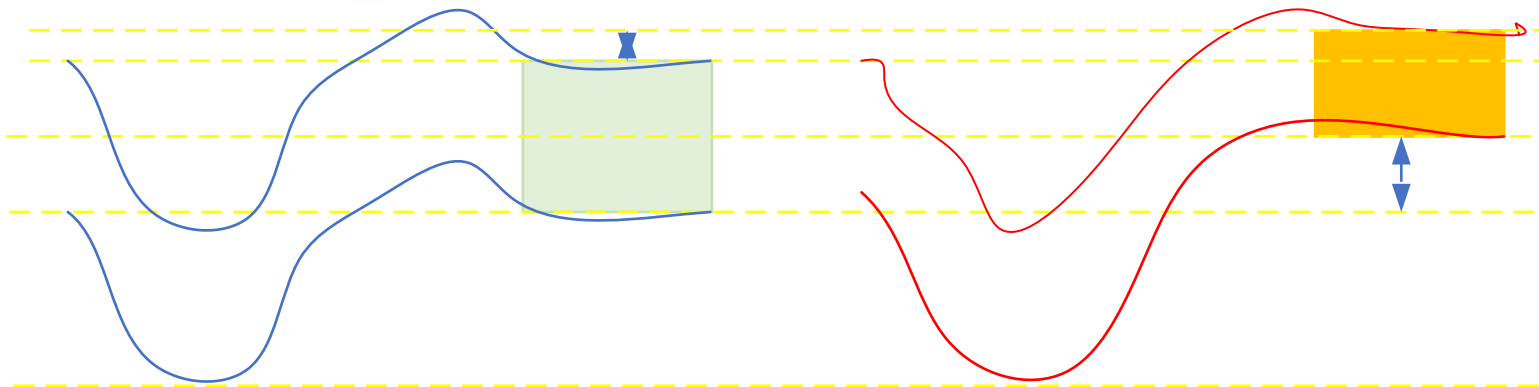
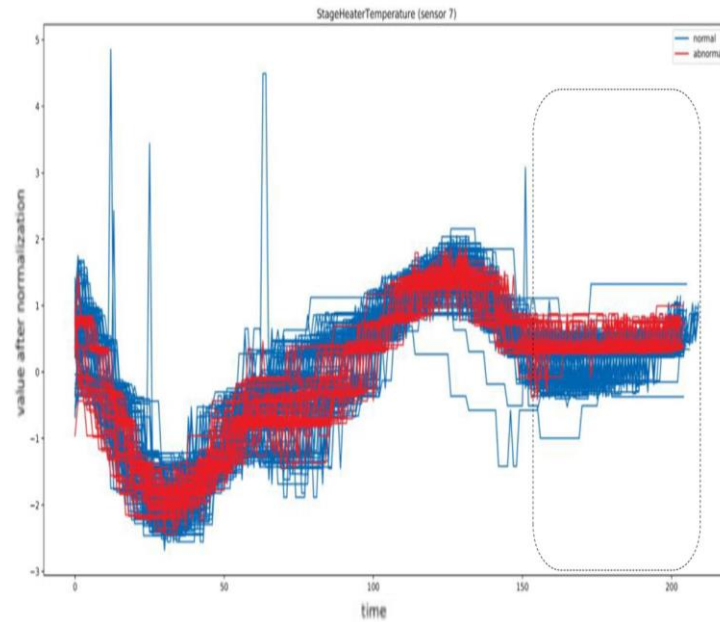


(b) in the testing dataset

“Multiple time-series convolutional neural network for fault detection and diagnosis and empirical study in semiconductor manufacturing” (4/6)



“Multiple time-series convolutional neural network for fault detection and diagnosis and empirical study in semiconductor manufacturing” (5/6)



“Multiple time-series convolutional neural network for fault detection and diagnosis and empirical study in semiconductor manufacturing” (6/6)

- Evaluation

Fivefolds cross-validation	Accuracy (%)
1NN-DTW (Xi et al. 2006)	70.88
SAX–VSM (Senin and Malinchik 2013)	85.66
Shapelet forests (Patri et al. 2014)	94.76
MC-DCNN (Zheng et al. 2014)	96.86
FDC-CNN (Lee et al. 2017b)	98.36
MTS-CNN	99.48

References

- K. Choi, J. Yi, C. Park and S. Yoon, "Deep Learning for Anomaly Detection in Time-Series Data: Review, Analysis, and Guidelines," in *IEEE Access*, vol. 9, pp. 120043-120065, 2021, doi: 10.1109/ACCESS.2021.3107975.
- Hsu, CY., Liu, WC. Multiple time-series convolutional neural network for fault detection and diagnosis and empirical study in semiconductor manufacturing. *J Intell Manuf* **32**, 823–836 (2021). <https://doi.org/10.1007/s10845-020-01591-0>